

L Number	Hits	Search Text	DB	Time stamp
3	5	039124.AP.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:18
4	3219	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210) or (257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (257/E27.098) or (257/E27.099) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.	USPAT; US-PGPUB	2004/03/20 18:54
5	0	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210) or (257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (257/E27.098) or (257/E27.099) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.) and (buried adj strap adj cell) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:28
6	0	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210) or (257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (257/E27.098) or (257/E27.099) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.) and (buried near4 strap adj cell) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:28
7	0	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210) or (257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (257/E27.098) or (257/E27.099) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.) and (body adj bias strap) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:29
8	13	(body adj bias strap) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:32
9	1	bit adj cell adj row.clm. and strap adj cell.clm. and offset adj supply adj line.clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:35
10	4	999361.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:35
11	1178	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.	USPAT; US-PGPUB	2004/03/20 18:47
12	7	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.) and body adj bias strap near6 bit adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 19:08
13	46	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.) and leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:51

14	14	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.) and leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:53
15	1	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.) and leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias) and strap adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:54
16	0	((257/204) or (257/205) or (257/206) or (257/207) or (257/208) or (257/210)).CCLS.) and leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias) and clamp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:54
17	1540	((257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.	USPAT; US-PGPUB	2004/03/20 18:54
18	16	((257/499) or (257/544) or (257/905) or (257/906) or (257/907) or (257/907) or (257/908) or (438/128) or (438/129) or (438/293) or (438/353) or (438/353) or (438/400)).CCLS.) and leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:57
19	1329	leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:57
20	72	leakage near6 (decrease decreased decreasing reduce reduces reduced reduction smaller lower improve improved improvement) and (strap strapping strapped body adj bias) and memory adj array.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:58
21	29782	H01L027/10.IPC.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 19:11
22	4	H01L027/10.IPC. and strap adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 19:08
23	17624	H01L027/10.IPC. and leakage and bit adj cell memory adj array.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 19:11
24	2	H01L027/10.IPC. and leakage and bit adj cell and memory adj array.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 19:12
-	333	(257/207).CCLS.	USPAT; US-PGPUB	2002/11/03 12:30
-	143	(257/499).CCLS.	USPAT; US-PGPUB	2002/11/03 12:30

-	189	(257/544).CCLS.	USPAT; US-PGPUB	2002/11/03 12:31
-	718	((257/544) or (257/207) or (257/499)).CCLS.	EPO; JPO; DERWENT;	2002/11/03 12:31
-	1376	((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/544) or (257/207) or (257/499)).CCLS.)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:31
-	0	((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/544) or (257/207) or (257/499)).CCLS.) and strap adj cell near12 bit adj cell near12 voltage	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/03/20 18:18
-	0	((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/544) or (257/207) or (257/499)).CCLS.) and strap adj cell near12 bit adj cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:32
-	0	strap adj cell near12 bit adj cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:33
-	115	strap adj cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:33
-	12	(strap adj cell) and 257/\$6.ccls.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:33
-	11	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 14:31
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj cell and strap adj cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:38
-	4	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj (line or cell) and strap adj cell	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:45
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj (line or cell) and strap adj cell and voltage near12 body near12 strap	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:40
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj (line or cell) and strap adj cell and voltage near15 body near15 strap	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:40
-	0	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj (line or cell) and strap adj cell and voltage near12 strap	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:41
-	1	((strap adj cell) and 257/\$6.ccls.) and (memory adj (device or cell) or sram or rom or eprom or "eprom/flash" or dram) and bit adj (line or cell) and strap adj cell and voltage near12 supply	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/03 12:45
-	4	(US-RE36837-\$ or US-6150686-\$ or US-5616961-\$ or US-5369049-\$).did.	IBM_TDB USPAT	2002/11/03 12:56

-	0	body near12 strap adj cell near12 (voltage or potential or bias or biased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 12:57
-	1	strap adj cell near12 (voltage or potential or bias or biased)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:02
-	0	("999361.ap.").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:02
-	3	999361.ap.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:02
-	0	buried adj strap adj cell near12 bias	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:32
-	146	(best or buried adj strap adj cell) near12 (bias or voltage or body or offset) near12 bit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:33
-	0	(best or buried adj strap adj cell) near12 (bias or voltage or body or offset) near12 bit adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:34
-	4	(best or buried adj strap adj cell) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:36
-	0	(buried adj strap adj cell) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:27
-	0	(buried adj strap) near12 (bias or voltage or body or offset) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:39
-	0	strap adj (line or cell or row or column) near12 (bias or voltage or body or offset) near12 bit adj (cell or line or row or column)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:41
-	0	strap adj (line or cell or row or column) near12 (bias or voltage or body or offset or potential) near12 bit adj (cell or line or row or column)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:42
-	1	strap near12 (bias or voltage or body or offset or potential) near12 bit adj (cell or line or row or column)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:42
-	0	(buried adj strap adj cell) near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:46

-	16	buried adj strap near12 bit adj (cell or line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:56
-	1	buried adj strap near12 bit adj (cell or line) and strap adj (line or cell)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/11/03 14:51
-	7	(US-6150686-\$ or US-RE36837-\$ or US-4724190-\$ or US-6455886-\$ or US-5616961-\$ or US-5369049-\$).did. or (US-20020080676-\$).did.	USPAT; US-PGPUB	2002/12/01 17:23
-	0	bit adj line and word adj line and dummy adj cell and body near12 (potential or voltage) and sram.ti,ab,clm. and leakage.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 17:25
-	895	bit adj line and word adj line and dummy adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 17:25
-	7	bit adj line and word adj line and dummy adj cell near12 body and (leakage or leaking or leak)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 18:25
-	1561	((257/204) or (257/205) or (257/206) or (257/207)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/02 22:29
-	4	((257/204) or (257/205) or (257/206) or (257/207)).CCLS.) and (bit-line or bit adj line or bitline) near12 dummy	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 18:55
-	1	((257/204) or (257/205) or (257/206) or (257/207)).CCLS.) and (strap adj cell or dummy adj cell) and gate adj array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:03
-	2	((257/204) or (257/205) or (257/206) or (257/207)).CCLS.) and (strap adj cell or dummy adj cell) and (leakage or leaking or leak)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 19:35
-	15	(strap adj cell or dummy adj cell) near15 body and (leakage or leaking or leak)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/01 19:36
-	92	(body adj bias or body adj strap or body adj contact) and memory.ti,ab,clm. and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:33
-	73	(body adj bias or body adj strap or body adj contact) and memory.ti,ab,clm. and 257/\$6.ccls. and (bit adj line or bitline or bit-line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:34
-	21	(body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.	USPAT; US-PGPUB	2002/12/11 09:36
-	0	(body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.	EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:36

-	1	(body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.	EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:37
-	1	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)	EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:37
-	22	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:45
-	2	("6018172").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 09:56
-	0	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:46
-	14	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 10:46
-	8	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage adj current	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:14
-	15	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage adj current and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:44
-	0	((body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and 257/\$6.ccls.) or ((body adj bias or body adj strap or body adj contact) near15 (bitline or bit-line or bit adj line) and memory.ti,ab,clm.)) and leakage adj current and cmos.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:36
-	1	(body adj bias or body adj strap or body adj contact) same (bitline or bit-line or bit adj line) and memory.ti,ab,clm. and (365/\$6.ccls. or 257/\$6.ccls.) and leakage adj current and cmos.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 16:58
-	1	(cmos or cmosfet).ti,ab,clm. and (body adj contact or body adj strap or body adj bias) near12 (seperate or each or both) near12 (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 17:02

-	1	(cmos or cmosfet).ti,ab,clm. and (body adj contact or body adj strap or body adj bias) near12 (separate or each or both) near12 (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 17:05
-	10	(cmos or cmosfet) and (body adj contact or body adj strap or body adj bias) near12 (separate or each or both) near12 (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 17:17
-	49	(cmos or cmosfet) and (body adj contact or body adj strap or body adj bias or body adj fixing or body adj potential) same (separate or each or both) same (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 18:28
-	19	(cmos or cmosfet) and (body adj contact or body adj strap or body adj bias or body adj fixing or body adj potential) same (separate or each or both) same (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET) same leakage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 18:34
-	20	(cmos or cmosfet) and (body adj node or body adj contact or body adj strap or body adj bias or body adj fixing or body adj potential) same (separate or each or both) same (NMOS or PMOS or n-channel or p-channel or NMOSFET or PMOSFET) same leakage	USPAT; US-PGPUB	2002/12/11 18:35
-	6	((("6128895") or ("6018172") or ("6104061"))).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/12 15:22
-	3	((("6128895") or ("6018172") or ("6104061"))).PN.	USPAT	2002/12/12 15:27
-	1	("6218895").PN.	USPAT	2002/12/12 15:27
-	19380	active adj region.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 15:51
-	3813	(active adj region.ti,ab,clm.) and 257/\$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 15:51
-	352	((active adj region.ti,ab,clm.) and 257/\$6.ccls.) and memory adj2 device.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 15:53
-	352	((active adj region.ti,ab,clm.) and 257/\$6.ccls.) and memory adj2 device.ti,ab,clm. and active adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 16:46
-	2	("6104061").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 16:47
-	7	"039124"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 16:47
-	557	257/e27.098.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:33

-	384	257/e27.099.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:09
-	872	257/e27.098.ccls. or 257/e27.099.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:09
-	195	(257/e27.098.ccls. or 257/e27.099.ccls.) and (leak or leakage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:10
-	165	((257/e27.098.ccls. or 257/e27.099.ccls.) and (leak or leakage)) and (well or n-well or p-well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:13
-	7	((257/e27.098.ccls. or 257/e27.099.ccls.) and (leak or leakage)) and (well or n-well or p-well)) and (body near3 strap or body near3 bias or body near3 contact)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:14
-	0	365/e27.098.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:34
-	384	(257/e27.099).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:35
-	788	(257/207).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:35
-	371	(257/499).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:35
-	302	(257/544).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:35
-	289	((257/905) or (257/906) or (257/907) or (257/908)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:37
-	4133	((257/288) or (257/296) or (257/297) or (257/205) or (257/206)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:38
-	0	("L14 or L15 or L16 or L16 or L17 or L18 or L19 or L20").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:39

-	51	((257/e27.098).CCLS.) or ((257/e27.099).CCLS.) or ((257/207).CCLS.) or ((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/905) or (257/906) or (257/907) or (257/908)).CCLS.) or ((257/288) or (257/296) or (257/297) or (257/205) or (257/206)).CCLS.) and (body near4 strap body near4 contact body near4 bias) and (well or n-well or n adj well or p-well or p adj well) and (leak or leakage or leaking)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:44
-	13	((257/e27.098).CCLS.) or ((257/e27.099).CCLS.) or ((257/207).CCLS.) or ((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/905) or (257/906) or (257/907) or (257/908)).CCLS.) or ((257/288) or (257/296) or (257/297) or (257/205) or (257/206)).CCLS.) and (body near4 strap body near4 contact body near4 bias) and (well or n-well or n adj well or p-well or p adj well) and (leak or leakage or leaking) and sram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 19:44
-	557	(257/e27.098).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 20:07
-	1613	contact adj hole and dram and (high adj density or high adj density)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 20:10
-	1245	contact adj hole and dram and (high adj density or high adj density) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 20:12
-	419	contact adj hole and dram.ti,ab,clm. and (high adj density or high adj density) and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/25 20:12
-	0	dummy adj cell near6 (body adj bias body adj contact body adj strap) and (MOS MOSFET CMOS CMOSFET field adj effect adj transistor FET).ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 16:41
-	0	dummy adj cell near6 (body adj bias body adj contact body adj strap) and (MOS MOSFET CMOS CMOSFET field adj effect adj transistor FET)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 16:42
-	0	dummy adj cell near6 (body adj bias body adj contact body adj strap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 16:43
-	1617	(dummy strap) near6 (body adj bias body adj contact body adj strap)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:00
-	48	((dummy strap) near6 (body adj bias body adj contact body adj strap)) and (mos mosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 18:30

-	6	((dummy strap) near6 (body adj bias body adj contact body adj strap)) and (mos mosfet) and (bit or bitline or bit adj cell or bit-line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 18:34
-	4	((dummy strap) near6 (body adj bias body adj contact body adj strap)) and (mos mosfet) and (bit or bitline or bit adj cell or bit-line) and (well p-well n-well p adj well n adj well)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 18:35
-	0	(dummy strap) near6 (body adj bias body adj contact body adj strap) and sram.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:01
-	6	(dummy strap) near6 (body adj bias body adj contact body adj strap) and (bitline bit-line or bit adj line)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:03
-	6505	((257/e27.098).CCLS.) or ((257/e27.099).CCLS.) or ((257/207).CCLS.) or ((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/905) or (257/906) or (257/907) or (257/908)).CCLS.) or ((257/288) or (257/296) or (257/297) or (257/205) or (257/206)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:20

-	2000	(US-5910667-\$ or US-5910666-\$ or US-5909047-\$ or US-5907503-\$ or US-5907502-\$ or US-5907170-\$ or US-5907166-\$ or US-5905278-\$ or US-5903493-\$ or US-5903035-\$ or US-5903026-\$ or US-5903024-\$ or US-5903023-\$ or US-5903022-\$ or US-5902121-\$ or US-5900763-\$ or US-5900676-\$ or US-5900659-\$ or US-5900658-\$ or US-5900657-\$ or US-5898677-\$ or US-5898636-\$ or US-5898194-\$ or US-5898186-\$ or US-5896313-\$ or US-5895942-\$).did. or (US-5894145-\$ or US-5894142-\$ or US-5892707-\$ or US-5892268-\$ or US-5892261-\$ or US-5892255-\$ or US-5892250-\$ or US-5889334-\$ or US-5920089-\$ or US-5920097-\$ or US-5917230-\$ or US-5917212-\$ or US-5917211-\$ or US-5917207-\$ or US-5917206-\$ or US-5914516-\$ or US-5914512-\$ or US-5914511-\$ or US-5914509-\$ or US-5914505-\$ or US-5912502-\$ or US-5912498-\$ or US-5910880-\$ or US-5936265-\$ or US-5936260-\$ or US-5936259-\$ or US-5932906-\$).did. or (US-5932905-\$ or US-5932900-\$ or US-5930163-\$ or US-5929506-\$ or US-5929499-\$ or US-5929495-\$ or US-5929477-\$ or US-5929476-\$ or US-5929475-\$ or US-5929469-\$ or US-5926706-\$ or US-5926359-\$ or US-5926064-\$ or US-5925904-\$ or US-5923089-\$ or US-5923062-\$ or US-5923060-\$ or US-5923048-\$ or US-5920110-\$ or US-5920107-\$ or US-5920105-\$ or US-5936292-\$ or US-5936286-\$ or US-5936285-\$ or US-5936273-\$ or US-5939744-\$ or US-5939743-\$).did. or (US-5942778-\$ or US-5942777-\$ or US-5940317-\$ or US-5939762-\$ or US-5969544-\$ or US-5969420-\$ or US-5969390-\$ or US-5969382-\$ or US-5966518-\$ or US-5966317-\$ or US-5965939-\$ or US-5965928-\$ or US-5965922-\$ or US-5965911-\$ or US-5963466-\$ or US-5962907-\$ or US-5962901-\$ or US-5960278-\$ or US-5959336-\$ or US-5959334-\$ or US-5959326-\$ or US-5959322-\$ or US-5959321-\$ or US-5959320-\$ or US-5959319-\$ or US-5956585-\$ or US-5955768-\$).did. or (US-5955757-\$ or US-5955756-\$ or US-5955753-\$ or US-5955746-\$ or US-5952687-\$ or US-5952684-\$ or US-5949705-\$ or US-5949116-\$ or US-5949112-\$ or US-5949110-\$ or US-5949100-\$ or US-5949098-\$ or US-5946581-\$ or US-5945846-\$ or US-5945730-\$ or US-5945704-\$ or US-5945702-\$ or US-5945698-\$ or US-5945696-\$ or US-5986294-\$ or US-5986293-\$ or US-5986292-\$ or US-5985709-\$ or US-5982008-\$ or US-5981995-\$ or US-5981989-\$ or US-5981987-\$).did. or (US-5981331-\$ or US-5979784-\$ or US-5977830-\$ or US-5977638-\$ or US-5977589-\$ or US-5977584-\$ or US-5977581-\$ or US-5977579-\$ or US-5977578-\$ or US-5977574-\$ or US-5977573-\$ or US-5977558-\$ or US-5976960-\$ or US-5976926-\$ or US-5973952-\$ or US-5973910-\$ or	USPAT; US-PGPUB	2003/05/26 19:18
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-	76	((257/e27.098).CCLS.) or ((257/e27.099).CCLS.) or ((257/207).CCLS.) or ((257/499).CCLS.) or ((257/544).CCLS.) or ((257/905) or (257/906) or (257/907) or (257/908)).CCLS.) or ((257/288) or (257/296) or (257/297) or (257/205) or (257/206)).CCLS.) and dummy adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:50
-	1532	cell adj array and (n-well or p-well) and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:52
-	54	cell adj array and dummy adj cell and (n-well or p-well) and memory.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:53
-	0	cell adj array and dummy adj cell and (n-well or p-well) and memory.ti,ab,clm. and fram and cmos	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:54
-	90	fram and cmos and cell adj2 array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:54
-	12	fram and cmos and cell adj2 array and dummy adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:57
-	0	fram and cmos.ti,ab,clm. and cell adj2 array and dummy adj cell	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 19:57
-	11	fram and cmos.ti,ab,clm. and cell adj2 array	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 20:23
-	557	(257/e27.098).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:54
-	2324	sram and flip-flop and inverter	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/26 20:34
-	2	("6420744").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:02
-	1307	sram and word and (bit-line or bit or bitline) and 365/\$6.ccls. and semiconductor near3 memory and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:56
-	78	sram and word and (bit-line or bit or bitline) and 365/\$6.ccls. and semiconductor near3 memory and substrate and (reduce or reduction) near6 leakage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 09:58

-	7	sram and word and (bit-line or bit or bitline) and 365/\$6.ccls. and semiconductor near3 memory and substrate and (reduce or reduction) near6 leakage adj current.ti,ab,clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/27 10:02
-	573	(365/182).CCLS.	USPAT; US-PGPUB	2003/05/27 10:37
-	1	("5281842").PN.	USPAT	2003/05/27 10:38
-	1	("6420744").PN.	USPAT	2003/05/27 10:38
-	1	("6337805").PN.	USPAT	2003/05/27 12:12
-	1	("6104061").PN.	USPAT	2003/11/02 22:20
-	1757	((257/204) or (257/205) or (257/206) or (257/207) or (257/E27.098) or (257/E27.099) or (257/499) or (257/544)).CCLS.	USPAT; US-PGPUB	2003/11/02 22:30
-	0	((257/204) or (257/205) or (257/206) or (257/207) or (257/E27.098) or (257/E27.099) or (257/499) or (257/544)).CCLS.) and bit adj cell and memory adj2 array.ti,ab,clm. and (strap adj line buried adj strap) and (bias voltage body offset off-set)	USPAT; US-PGPUB	2003/11/02 22:33
-	1	((257/204) or (257/205) or (257/206) or (257/207) or (257/E27.098) or (257/E27.099) or (257/499) or (257/544)).CCLS.) and bit adj cell and memory adj2 array.ti,ab,clm. and (strap adj line buried adj strap strap adj cell)	USPAT; US-PGPUB	2003/11/02 22:33
-	4841	((438/128) or (438/129) or (257/218) or (438/219) or (438/293) or (438/353) or (438/400) or (257/207) or (257/499) or (257/544)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/11/03 09:27
-	10	((438/128) or (438/129) or (257/218) or (438/219) or (438/293) or (438/353) or (438/400) or (257/207) or (257/499) or (257/544)).CCLS.) and (strap adj cell buried adj strap body adj strap body adj bias)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/03/20 18:22
-	2	("6420744").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 18:51
-	43	erratico.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/21 18:51